

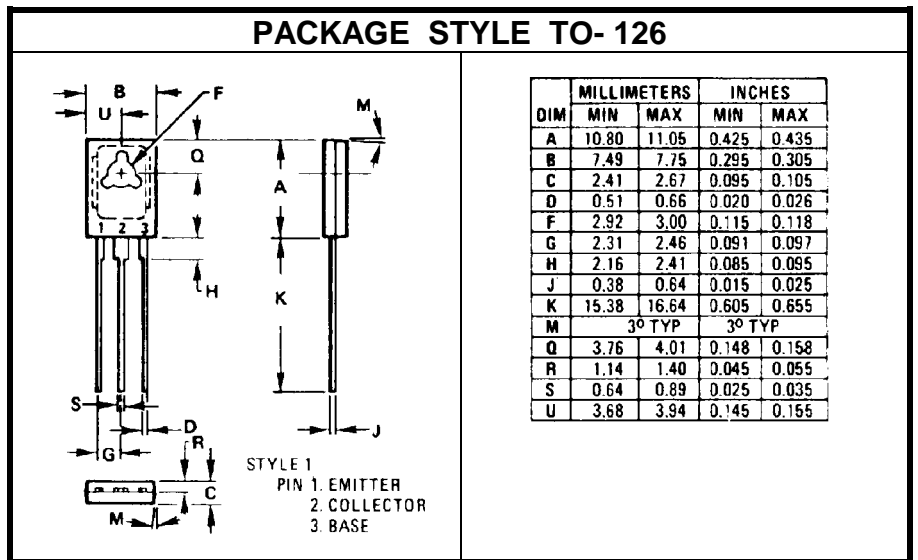
NPN SILICON HIGH FREQUENCY TRANSISTOR

DESCRIPTION:

The **ASI BFT51F.A** is Designed for High Frequency Amplifier Applications.

MAXIMUM RATINGS

I_C	500 mA
V_{CE}	20 V
P_{DISS}	3.0 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+175^\circ\text{C}$
T_{STG}	-65°C to $+175^\circ\text{C}$
θ_{JC}	50°C/W


CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 5.0\text{ mA}$	10			V
BV_{CER}	$I_C = 1.0\text{ mA}$ $R_{BE} = 100\ \Omega$	18			V
BV_{CBO}	$I_C = 1.0\text{ mA}$	20			V
I_{CEO}	$V_{CE} = 5.0\text{ V}$			1.0	mA
I_{CES}	$V_{CE} = 10\text{ V}$			100	μA
I_{EBO}	$V_{EB} = 3.0\text{ V}$			1.0	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 100\text{ mA}$ $I_C = 300\text{ mA}$	40			---
f_t	$V_{CE} = 5.0\text{ V}$ $I_C = 300\text{ mA}$ $f = 100\text{ MHz}$	1.0	2.0		GHz
C_{ob}	$V_{CB} = 5.0\text{ V}$ $f = 1.0\text{ MHz}$		4.0		pF